

Structural and magnetic properties of transition metal substituted ZnO

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(Dated: February 2, 2008)

Structural and magnetic properties have been studied for polycrystalline $\text{Zn}_{1-x}\text{TM}_x\text{O}$, where TM (transition metal ions) = Mn, Fe, and Co. No bulk ferromagnetism was observed for single-phase materials, contrary to the existing theories. Single-phase samples demonstrate paramagnetic Curie-Weiss behavior with antiferromagnetic interactions, similar to other diluted magnetic semiconductors. Non-optimal synthesis conditions lead to formation of second phases that are responsible for spin-glass behavior (ZnMnO_3 impurity for $\text{Zn}_{1-x}\text{Mn}_x\text{O}$ (S. Kolesnik *et al.*, J. Supercond.: Inorp. Novel Magn. **15**, 251 (2002))) or high-temperature ferromagnetic ordering (Co metal for $\text{Zn}_{1-x}\text{Co}_x\text{O}$ with the Curie temperature $T_C > 800$ K or $(\text{Zn,Fe})_3\text{O}_4$ for $\text{Zn}_{1-x}\text{Fe}_x\text{O}$ with $T_C = 440$ K).

Keywords: Diluted magnetic semiconductors, ZnO, synthesis, ferromagnetism

I. INTRODUCTION

A widegap II-VI semiconductor, ZnO attracts attention as a material with possible application in optoelectronic devices such as solar cells, ultraviolet emitting diodes and transparent high-power electronic devices. The discovery of ferromagnetism at temperatures above 100 K in the III-V semiconductor $\text{Ga}_{1-x}\text{Mn}_x\text{As}$ [1] provided practical means to incorporate spin into semiconductor electronics. Theoretical predictions of room temperature ferromagnetism in diluted magnetic semiconductors [2] recently focused attention on magnetic-ion-substituted ZnO with a wurtzite structure similar to GaAs. According to these calculations, room temperature ferromagnetism can exist in p -type doped $\text{Zn}_{1-x}\text{Mn}_x\text{O}$ with 5%Mn and $3.5 \cdot 10^{20}$ holes per cm^3 . *Ab initio* band calculations [3] predict stability of ferromagnetism in p -type $\text{Zn}_{1-x}\text{Mn}_x\text{O}$, and antiferromagnetism in n -type $\text{Zn}_{1-x}\text{Mn}_x\text{O}$. Similar calculations predict a ferromagnetic phase for both carrier-undoped and n -type ZnO substituted with Fe, Co, or Ni. [4] The parent compound ZnO without intentional carrier doping shows n -type conduction related to oxygen vacancies and Zn interstitials. [5] The introduction of p -type conduction in ZnO is difficult. Several methods, including nitrogen doping [5, 6] and Ga and N codoping [7, 8], have been reported. Successful preparation of p -type ZnO could allow fabrication of transparent $p-n$ junctions and could enable synthesis of substituted ferromagnets.

Pulsed-laser deposited $\text{Zn}_{1-x}\text{Mn}_x\text{O}$ thin films with up to 35% Mn show spin-glass behavior. [9] We have previously shown for polycrystalline $\text{Zn}_{1-x}\text{Mn}_x\text{O}$ that the spin-glass behavior can be induced by high-pressure oxygen annealing and it is related to precipitation of impurity phase ZnMnO_3 . [10] ZnO films doped with Co have been reported to be ferromagnetic with Curie temperature of about 280 K. [11] However, Kim *et al.* pointed to the presence of Co clusters in their thin films as a reason for room temperature ferromagnetism. [12] High-temperature ferromagnetism in thin films of Co-doped anatase TiO_2 [13] has also been explained by the fact that

cobalt is not substitutional for titanium in TiO_2 . [14] In this study, we investigate polycrystalline $\text{Zn}_{1-x}\text{TM}_x\text{O}$, where TM = Mn, Fe, and Co. We show that no high-temperature ferromagnetic ordering is present in single-phase samples. Ferromagnetism in these materials can be induced by second phases that may appear after non-optimal synthesis conditions.

II. EXPERIMENTAL METHODS

The $\text{Zn}_{1-x}\text{TM}_x\text{O}$ samples in this study were prepared using a standard solid-state reaction technique. Mixtures of ZnO and MnO_2 , Fe_2O_3 , or Co_3O_4 , for TM = Mn, Fe, and Co, respectively, were fired in air several times at elevated temperatures 900, 1000, 1100, and 1200°C with intermediate grindings. The samples were then annealed in an atmosphere of various gases (Ar, H_2 , 1% H_2 /Ar, and O_2 under high pressure of 600 bar). High pressure oxygen annealing was intended to produce p -type doped ZnO materials. Magnetic ac susceptibility and dc magnetization were measured using a Physical Property Measurement System and a Magnetic Property Measurement System (both Quantum Design) at temperatures up to 400 and 800 K, respectively. Energy dispersive x-ray spectroscopy (EDXS) analysis was performed by a Hitachi S-4700-II scanning electron microscope. Typically, 15-20 EDXS spectra were collected for each composition at various locations across the surface of a sintered pellet. Using the average Zn and TM cation contents, which were obtained from the EDXS spectra we determined the effective composition $\text{Zn}_{1-x_{\text{eff}}}\text{TM}_{x_{\text{eff}}}\text{O}$ of the studied samples. X-ray diffraction experiments have been performed using a Rigaku x-ray diffractometer. We have analyzed the x-ray diffraction patterns using the Rietveld technique with the General Structure GSAS code.[15] The refinements were done using the wurtzite hexagonal space group $\text{P6}_3\text{mc}$ with (Zn,TM) atoms located at $(2/3, 1/3, 0)$ and O atoms located at $(2/3, 1/3, u)$. For both single-phase and multi-phase samples (where impurity peaks were observed), this was the only phase refined.

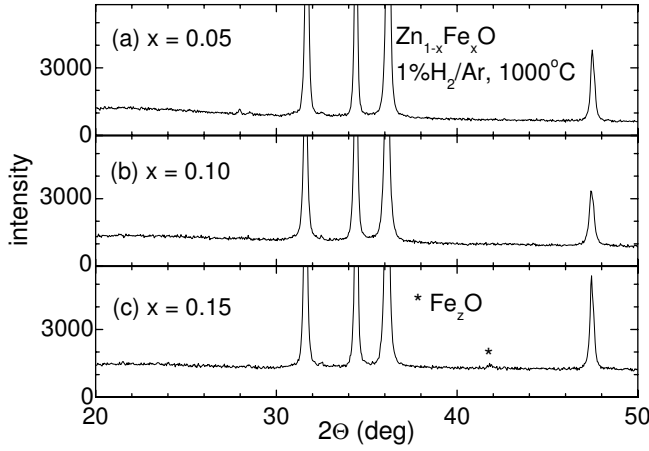


FIG. 1: X-ray diffraction patterns for $\text{Zn}_{1-x}\text{Fe}_x\text{O}$ samples synthesized in $1\%\text{H}_2/\text{Ar}$ at 1000°C .

III. RELATIONSHIP BETWEEN SYNTHESIS CONDITIONS AND STRUCTURAL PROPERTIES

Single-phase samples can be synthesized in air for $\text{TM} = \text{Mn}$, and Co and in $1\%\text{H}_2/\text{Ar}$ for $\text{TM} = \text{Fe}$. X-ray diffraction data show that the $\text{Zn}_{1-x}\text{TM}_x\text{O}$ samples are single-phase with the wurtzite structure up to a certain value of x . We estimated this value (the solubility limit) to be equal to 0.1, 0.1, and 0.2 for $\text{TM} = \text{Mn}$, Fe , and Co , respectively. Above the solubility limit, characteristic impurities can be observed by x-ray diffraction, namely ZnMn_2O_4 , Fe_2O or $(\text{Zn,Fe})_3\text{O}_4$, and CoO for $\text{TM} = \text{Mn}$, Fe , and Co , respectively.

In Fig. 1 X-ray diffraction patterns are presented for $\text{Zn}_{1-x}\text{Fe}_x\text{O}$ after synthesis in $1\%\text{H}_2/\text{Ar}$ at 1000°C . The samples with $x \leq 0.1$ are single-phase, and the presence of the second phase Fe_2O can be observed for $x \geq 0.15$. Wüstite Fe_2O can typically be obtained in a slightly non-stoichiometric form with $z < 1$ depending on synthesis conditions; however, due to a very small amount of this phase in the $\text{Zn}_{0.85}\text{Fe}_{0.15}\text{O}$ sample, we could not determine the value of z . Thus, we have separately prepared wüstite Fe_2O by reduction of Fe_2O_3 in the same atmosphere, $1\%\text{H}_2/\text{Ar}$ at 1050°C , and obtained the compound with the rock-salt structure and lattice constant $a = 4.3101 \text{ \AA}$ that is consistent with $z = 0.95$. Stability of $\text{Zn}_{1-x}\text{Fe}_x\text{O}$ and second phases are sensitive to changes of the synthesis temperature. The annealing of these samples in $1\%\text{H}_2/\text{Ar}$ at 950°C leads to precipitation of second phase $(\text{Zn,Fe})_3\text{O}_4$, which accounts for room temperature ferromagnetism in multi-phase $\text{Zn}_{1-x}\text{Fe}_x\text{O}$. Substitution of Fe in ZnO is not possible in air or at high pressure of oxygen at any temperature.

Fig. 2 shows x-ray diffraction patterns for the $\text{Zn}_{0.8}\text{Co}_{0.2}\text{O}$ sample obtained from several annealing conditions. Various impurity peaks appear after annealing under reducing or strongly oxidizing conditions. These peaks are marked with stars in Fig. 2. After argon

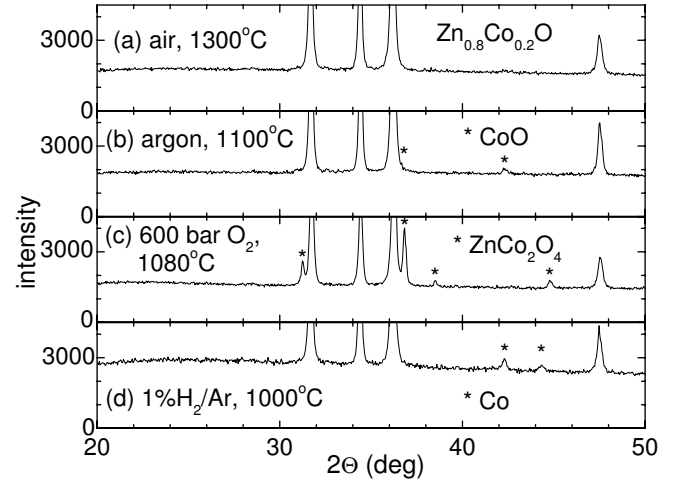


FIG. 2: X-ray diffraction patterns for $\text{Zn}_{0.8}\text{Co}_{0.2}\text{O}$ samples synthesized in air (a), argon-annealed (b), high-pressure oxygen-annealed (c), and (d) slightly reduced in $1\%\text{H}_2/\text{Ar}$ at 1000°C .

annealing at $T = 1100^\circ\text{C}$, rock-salt-like antiferromagnetic CoO impurity is present. A slight reduction of $\text{Zn}_{0.8}\text{Co}_{0.2}\text{O}$ in $1\%\text{H}_2/\text{Ar}$ at 1000°C leads to precipitation of Co metal, which causes a ferromagnetic contribution to the measured ac susceptibility and dc magnetization. High-pressure oxygen annealing at $T = 1080^\circ\text{C}$ induces spinel-like ZnCo_2O_4 impurity. High-pressure oxygen annealing was found, thus, to favor formation of compounds other than $\text{Zn}_{1-x}\text{TM}_x\text{O}$, for which TM ions display oxidation states higher than 2+.

Structural parameters of $\text{Zn}_{1-x}\text{TM}_x\text{O}$ obtained from the Rietveld refinements are presented in Fig. 3. Open symbols in Fig. 3 denote the multi-phase compositions, i.e. the ones for which the presence of impurity peaks is observed in the X-ray diffraction data. The unit cell volume changes almost linearly with substitution of TM for single-phase compositions. This behavior is expected according to the difference between ionic radii r of tetrahedrally coordinated Zn^{2+} $r = 0.60 \text{ \AA}$ and other transition metal TM^{2+} ions ($r = 0.66, 0.63$, and $0.58 \text{ \AA}$ for $\text{TM} = \text{Mn, Fe, and Co}$, respectively). [16] The observed slight increase of the cell volume in case of $\text{TM} = \text{Co}$ is inconsistent with the smaller ionic radius of Co than Zn estimated by Shannon. [16] This increase can not be explained either by the presence of Co^{3+} in $\text{Zn}_{1-x}\text{Co}_x\text{O}$ as Co^{3+} is smaller than Co^{2+} . [16] Apparently, the ionic size of tetrahedrally coordinated Co^{2+} ion is larger than that of Zn^{2+} . The u parameter (z -coordinate of the oxygen atoms) of the wurtzite structure of $\text{Zn}_{1-x}\text{TM}_x\text{O}$ initially increases with increasing x , reaches its maximum close to the solubility limit, and subsequently decreases. The c/a ratio [Fig. 3(d)] decreases slightly at a similar rate for $\text{TM} = \text{Mn}$ and Co , while it decreases much more rapidly for $\text{TM} = \text{Fe}$. This effect shows that Fe -doped ZnO is more anisotropic than ZnO doped with other transition metal ions. Ref. [17] has shown a phenomenological lin-

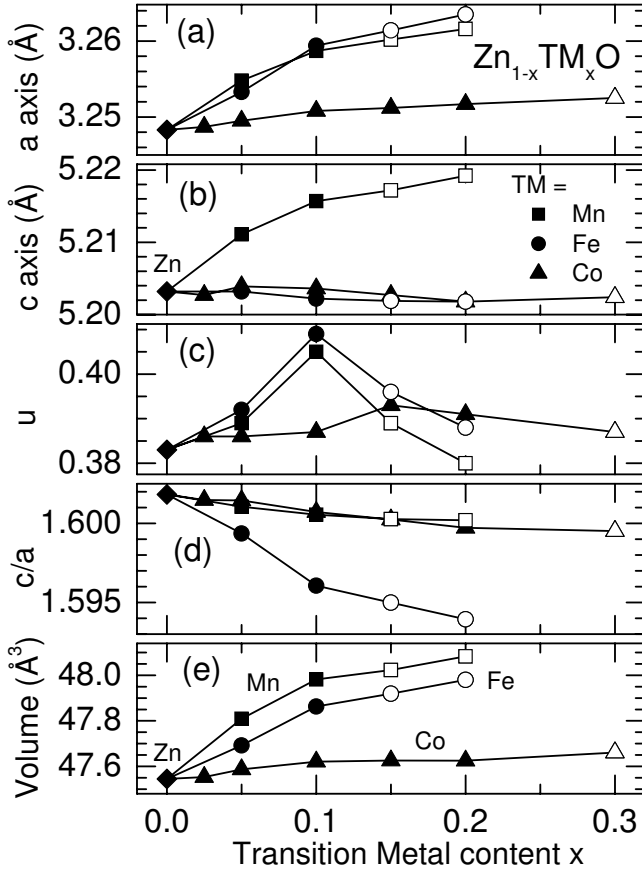


FIG. 3: Lattice parameters a (a), c (b), u - parameter of the wurtzite structure (c), c/a ratio (d), and unit cell volume (e) determined from the X-ray diffraction patterns for $\text{Zn}_{1-x}\text{TM}_x\text{O}$ samples. Full symbols denote single-phase samples, open symbols denote multi-phase samples.

ear dependence $u \propto (a/c)^2$ for all undoped wurtzite-like compounds including ZnO. Our observation for transition metal doped ZnO is qualitatively consistent with this tendency up to the solubility limit. The coefficient of this linear dependence (varying from 9 to 34) is much higher than the reported value of $1/3$. [17]

The effective TM content x_{eff} in $\text{Zn}_{1-x}\text{TM}_x\text{O}$ determined from EDXS analysis is presented in Fig. 4. In our previous work [10] we have shown (based on the assumption that the ac susceptibility reflects spin-only behavior) that $x_{\text{eff}} < x$ for TM = Mn (solid line in Fig. 4.) Present EDXS data for TM = Mn confirm that result. For TM = Co, we observe a good agreement between the effective and nominal TM contents, within the experimental error. For TM = Fe, $x_{\text{eff}} \simeq x$ for $x = 0.05$. However, for higher Fe concentration, $x = 0.1$, we observe $x_{\text{eff}} \simeq 0.14$. This larger effective Fe content than the starting content, x , could arise from Zn volatilization during synthesis under reducing conditions in $1\%\text{H}_2/\text{Ar}$. We did not include this composition for the analysis of the magnetic properties of $\text{Zn}_{1-x}\text{Fe}_x\text{O}$.

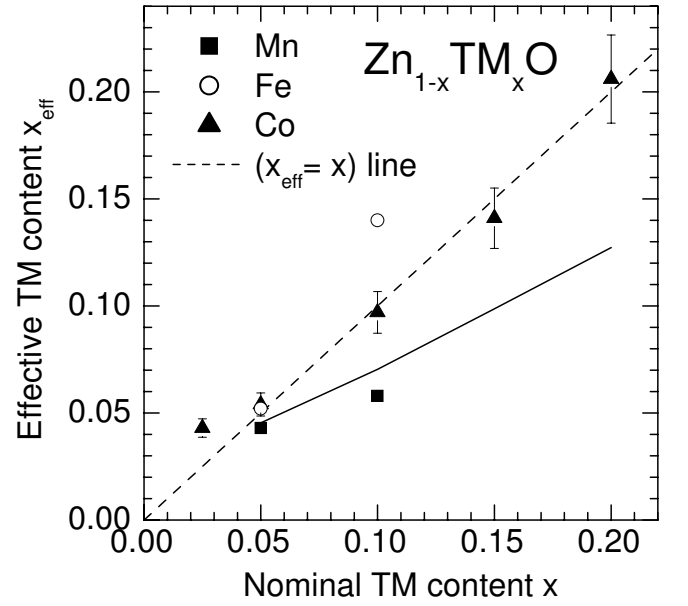


FIG. 4: The effective TM content in $\text{Zn}_{1-x}\text{TM}_x\text{O}$ determined from the EDXS analysis. Solid line shows x_{eff} for TM = Mn determined from the ac susceptibility (see: Ref. [10]).

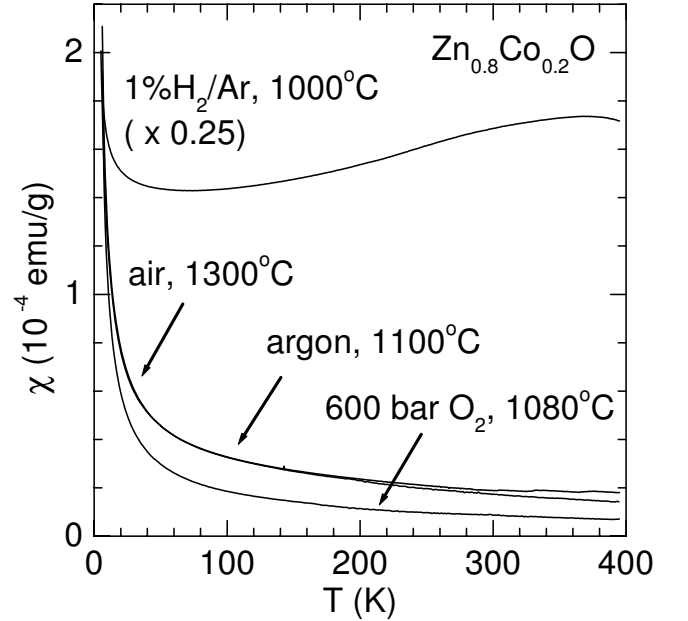


FIG. 5: Magnetic ac susceptibility for $\text{Zn}_{0.8}\text{Co}_{0.2}\text{O}$ samples synthesized under different conditions.

IV. MAGNETIC PROPERTIES

Magnetic susceptibility is presented in Fig. 5 for $\text{Zn}_{0.8}\text{Co}_{0.2}\text{O}$. Here and throughout this paper, the diamagnetic ac susceptibility of $-0.33 \cdot 10^{-6} \text{ emu/g}$ for ZnO [18] was subtracted from the measured magnetic susceptibility. The ac susceptibility of the TM-doped ZnO resembles Curie-Weiss behavior which is also characteris-

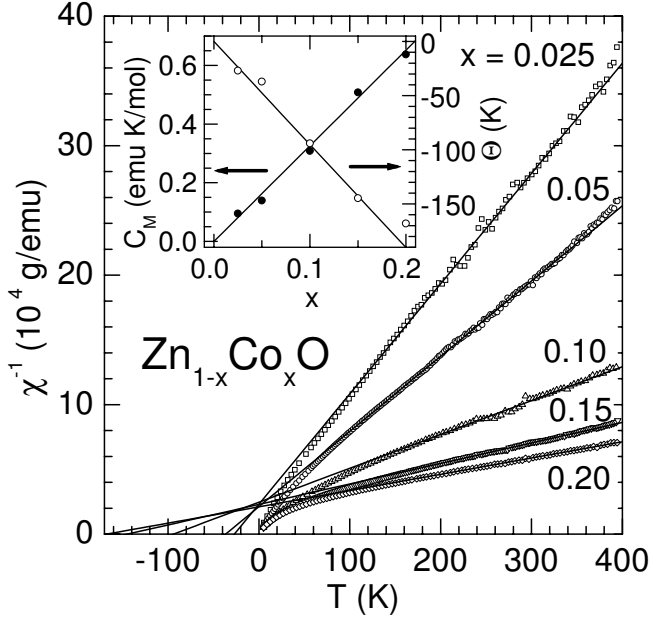


FIG. 6: Inverse magnetic susceptibility for $\text{Zn}_{1-x}\text{Co}_x\text{O}$ samples. The inset shows molar Curie constants C_M (full symbols) and Curie-Weiss temperatures Θ (open symbols).

tic for other TM-containing semimagnetic semiconductors. [19] The annealing in Ar under atmospheric pressure (which is correlated to the appearance of antiferromagnetic CoO impurity [Fig. 2(b)]) does not significantly change the value of the ac susceptibility. A significant decrease of the ac susceptibility can be observed after high-pressure oxygen annealing. After this annealing, a spinel-like ZnCo_2O_4 second phase [Fig. 2(c)] is present in the sample. The most dramatic change of the magnetic properties of $\text{Zn}_{1-x}\text{Co}_x\text{O}$ can be observed after annealing in 1% H_2/Ar at 1000°C. The sample becomes ferromagnetic at a temperature higher than 800 K. This ferromagnetic behavior is a result of the presence of Co-metal impurity in the compound [Fig. 2(d)].

Inverse magnetic susceptibility for $\text{Zn}_{1-x}\text{Co}_x\text{O}$ is shown in Fig. 6. The behavior presented here is characteristic to all studied TM-doped ZnO samples. These results, for TM = Mn, were presented elsewhere. [10] We have analyzed ac susceptibility results within the framework of the diluted Heisenberg antiferromagnet theory of Spalek *et al.* [19] Although this theory was developed for larger group VI elements, Se, Te, and S, we use it here also for the oxygen ion. At higher temperatures, the ac mass susceptibility can be described by the formula

$$\chi = \frac{C_M(x)}{T - \Theta(x)}, \quad (1)$$

where $\Theta(x) = \Theta_0 \cdot x$ is the Curie-Weiss temperature, $C_M(x) = C_0 \cdot x$ is the molar Curie constant and C_0 is defined as

$$C_0 = \frac{N(g_{\text{eff}}\mu_B)^2 S(S+1)}{3k_B\rho}, \quad (2)$$

N is the number of cations per unit volume, g_{eff} is the effective gyromagnetic factor of TM^{2+} ion, S is the spin, and ρ is the mass density calculated from the lattice parameters. The constant Θ_0 is related to the exchange integral between the nearest TM neighbors J_1 ,

$$\frac{2J_1}{k_B} = \frac{3\Theta_0}{zS(S+1)}, \quad (3)$$

where $z = 12$ is the number of nearest neighbors in the wurtzite structure of $\text{Zn}_{1-x}\text{TM}_x\text{O}$.

A linear fit to the inverse susceptibility data intersects the $\chi^{-1} = 0$ axis at a negative temperature. This result indicates the presence of antiferromagnetic interactions in the $\text{Zn}_{1-x}\text{TM}_x\text{O}$ samples. At lower temperatures, inverse ac susceptibility deviates from the linear dependence toward a temperature close to zero. This is a result of additional antiferromagnetic interactions between the next nearest neighbor TM ions. [19]. The inset to Fig. 6 shows the molar Curie constants and the Curie-Weiss temperatures for $\text{Zn}_{1-x}\text{Co}_x\text{O}$. From linear fits of C_M and Θ as a function of x , we have determined the parameters C_0 and Θ_0 for the studied TM-doped ZnO samples. The constant C_0 contains both the spin of the TM^{2+} ions and the effective g_{eff} factor. Mn^{2+} -substituted ZnO was already discussed in Ref. [10] Due to the half-filled 3d shell of Mn^{2+} , its orbital momentum $L = 0$, the spin is $S = 5/2$, and the g_{eff} factor is very close to the free-spin value $g = 2$. This is similar to other Mn-based diluted magnetic semiconductors. For Co^{2+} , the splitting of the energy levels due to the strong spin-orbit interaction results in an increase of the effective g_{eff} factor. The values of $g_{\text{eff}} = 2.24\text{--}2.31$ were reported for Co^{2+} in different diluted magnetic semiconductors. [22, 23, 24, 25, 26] An enhanced g_{eff} factor is also expected for Fe^{2+} due to its large orbital momentum ($L = 2, S = 2$). [27]

TABLE I: Material parameters determined from ac susceptibility for $\text{Zn}_{1-x}\text{TM}_x\text{O}$.

TM ion	Θ_0 (K)	C_0 (emu K/mol)	$2J_1/k_B$ (K)	spin S	g_{eff}
Mn	-961 ± 49	4.1 ± 0.2	-27.5 ± 1.4	5/2	2
Fe	-926 ± 26	6.0 ± 0.1	-38.6 ± 1.1	2	2.83
Co	-951 ± 110	3.3 ± 0.1	-63.4 ± 7.4	3/2	2.64

In Table I, we compare the results determined from ac susceptibility for our samples with different TM^{2+} . Here we assume the spin S to be equal to the theoretically expected value for each particular TM^{2+} ion. Our values of Θ_0 and $2J_1/k_B$ are similar to other TM-containing semiconductors in case of TM = Mn [19, 21] and TM = Co. [26] The effective g_{eff} factors for TM = Co and Fe are substantially larger than the values from literature for other diluted magnetic semiconductors doped with respective TM^{2+} ions. The origin of this large g_{eff} factor is not clear at the moment. The presence of a small number of TM^{3+} in our samples (not detectable by X-ray

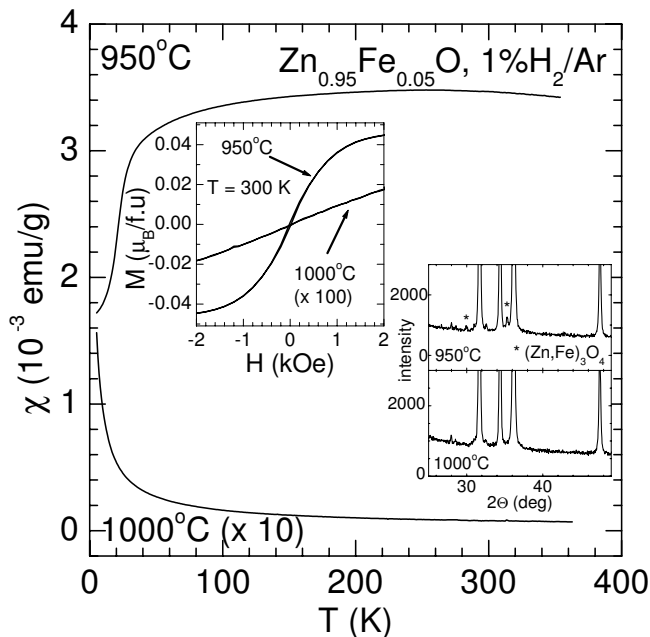


FIG. 7: Magnetic ac susceptibility (main panel), dc magnetization at $T = 300$ K, and X-ray diffraction patterns for $\text{Zn}_{0.95}\text{Fe}_{0.05}\text{O}$ synthesized in $1\%\text{H}_2/\text{Ar}$ at 950°C and 1000°C .

diffraction) is one possibility. These ions can increase the effective spin above the assumed value for TM^{2+} . This effect is especially crucial in the case of Fe substituted ZnO which we discuss below.

The influence of synthesis conditions on the structural and magnetic properties of $\text{Zn}_{0.95}\text{Fe}_{0.05}\text{O}$ is illustrated in Fig. 7. The sample annealed at 950°C shows the presence of magnetite-like $(\text{Zn,Fe})_3\text{O}_4$ impurity as displayed in the right inset. The ac susceptibility of this sample is much larger than the paramagnetic susceptibility of pure $\text{Zn}_{0.95}\text{Fe}_{0.05}\text{O}$ (annealed at 1000°C). The temperature dependence of ac susceptibility for the sample containing $(\text{Zn,Fe})_3\text{O}_4$ impurity is flat at higher temperatures, which is related to a ferromagnetic order with the Curie temperature equal to 440 K. A drop of the ac susceptibility around 20 K is probably related to the low temperature Verwey transformation, similar to the one observed in stoichiometric Fe_3O_4 at 120 K. [28] The left inset to Fig. 7 shows the magnetization curves at $T = 300$ K for both samples. The $(\text{Zn,Fe})_3\text{O}_4$ -containing sample shows a narrow ferromagnetic hysteresis curve

and the saturation magnetization close to $0.05\mu_B$ per formula unit, which is equal to $1\mu_B$ per substituting Fe ion. For ferrimagnetically coupled Fe ions in Fe_3O_4 one would expect the saturation magnetization $1.33\mu_B$ per Fe ion. This suggests that most of the Fe in the multi-phase $\text{Zn}_{0.95}\text{Fe}_{0.05}\text{O}$ sample is precipitated as a $(\text{Zn,Fe})_3\text{O}_4$ impurity. The single-phase $\text{Zn}_{0.95}\text{Fe}_{0.05}\text{O}$ sample shows a linear paramagnetic dependence on the magnetic field with a very small ferromagnetic hysteretic contribution. We were able to determine the magnitude of this ferromagnetic contribution by the following numerical procedure. Linear fits of the $M(H)$ data were performed in the high-field ranges 40 to 70 kOe and -40 to -70 kOe, where the ferromagnetic contribution to the magnetization is expected to be fully saturated. The average of the two fitted lines was subtracted from the measured $M(H)$ dependence. As a result, we obtained a small ferromagnetic hysteresis curve. The saturation magnetization of this ferromagnetic contribution gives an estimate for the upper limit of the ferromagnetic $(\text{Zn,Fe})_3\text{O}_4$ impurity of 0.1% .

V. SUMMARY

In summary, by studying structural and magnetic properties of transition metal substituted polycrystalline ZnO samples, we have found that no bulk ferromagnetism exists for single-phase materials, contrary to the existing theories. Stoichiometric samples demonstrate paramagnetic behavior with antiferromagnetic interactions similar to other semimagnetic semiconductors substituted with transition metal ions. Selected synthesis conditions lead to impurity-induced ferromagnetic order in Co- and Fe-doped ZnO. Attempts to induce p -type doping by high-pressure oxygen synthesis lead to formation of secondary phases for which transition metals Mn, Fe, and Co exist in high oxidation states.

Acknowledgments

This work was supported by NSF (DMR-0302617), the U.S. Department of Education, and the State of Illinois under HECA. The EDXS analysis was performed in the Electron Microscopy Center, Argonne National Laboratory, Argonne, IL.

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